

Can electrical phenomena be explained with the concept of an "electric family tree"?

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Change in the parameters of electron-irradiated 4H-SiC Schottky diodes as a function of the time during low-temperature isothermal annealing

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Comparative results of low temperature annealing of lightly doped n-layers of silicon carbide irradiated by protons and electrons

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Corrected accounting of electron-hole scattering in cross-term current equations for Si and SiC

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